



CPH6329 — P-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		-30	V
Gate-to-Source Voltage	V _{GSS}		±10	V
Drain Current (DC)	I _D		-2.0	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	-8.0	A
Allowable Power Dissipation	P _D	Mounted on a ceramic board (900mm ² X0.8mm)	1.2	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _{GS} =0	-30			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =-30V, V _{GS} =0			-1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±8V, V _{DS} =0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} =-10V, I _D =-1mA	-0.4		-1.4	V
Forward Transfer Admittance	y _{fs}	V _{DS} =-10V, I _D =-1.0A	1.4	2.4		S
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =-1.0A, V _{GS} =-4V		215	280	mΩ
	R _{DS(on)2}	I _D =-0.5A, V _{GS} =-2.5V		290	410	mΩ
Input Capacitance	C _{iss}	V _{DS} =-10V, f=1MHz		285		pF
Output Capacitance	C _{oss}	V _{DS} =-10V, f=1MHz		52		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =-10V, f=1MHz		38		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		10		ns
Rise Time	t _r	See specified Test Circuit.		33		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		28		ns
Fall Time	t _f	See specified Test Circuit.		33		ns

Marking : YF

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CPH6329

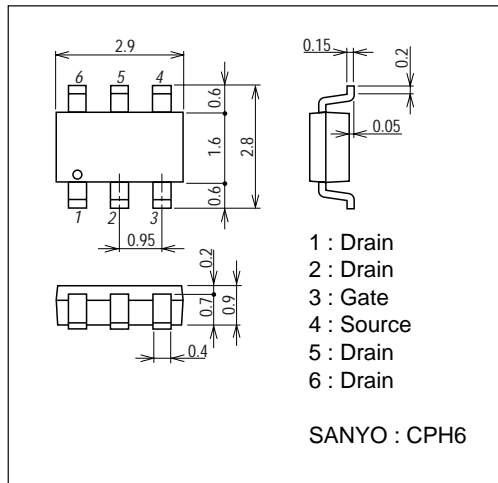
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	$V_{DS}=-10V, V_{GS}=-4V, I_D=-2.0A$		2.6		nC
Gate-to-Source Charge	Qgs	$V_{DS}=-10V, V_{GS}=-4V, I_D=-2.0A$		0.78		nC
Gate-to-Drain "Miller" Charge	Qgd	$V_{DS}=-10V, V_{GS}=-4V, I_D=-2.0A$		0.64		nC
Diode Forward Voltage	VSD	$I_S=-2.0A, V_{GS}=0$		-0.93	-1.5	V

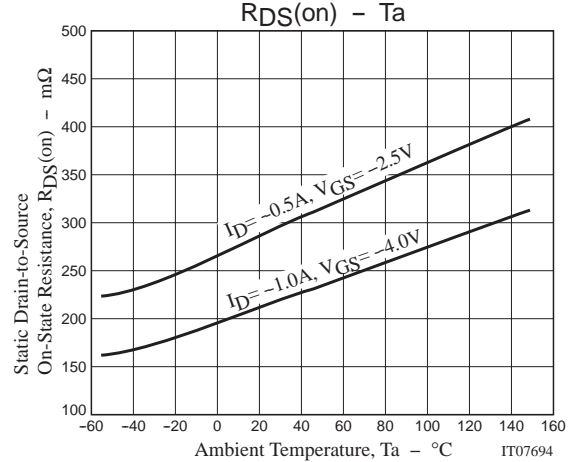
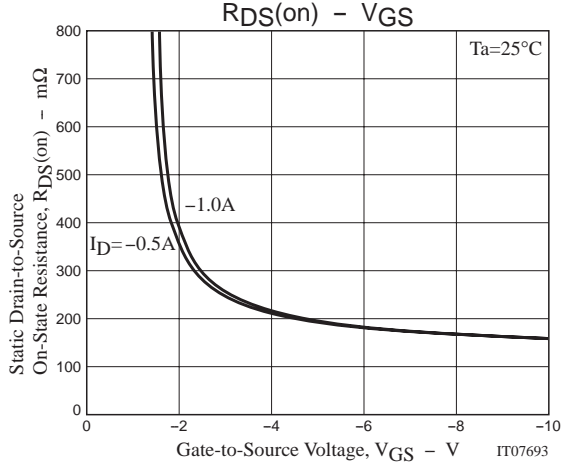
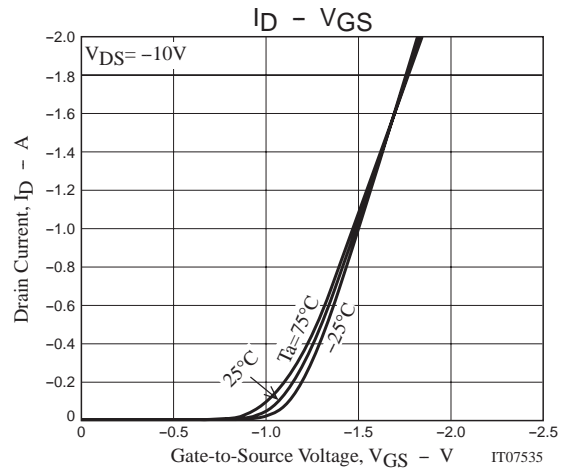
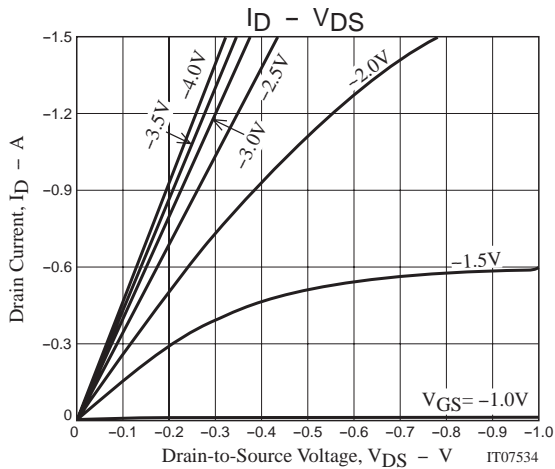
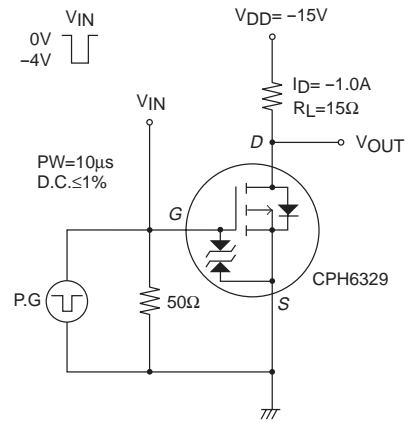
Package Dimensions

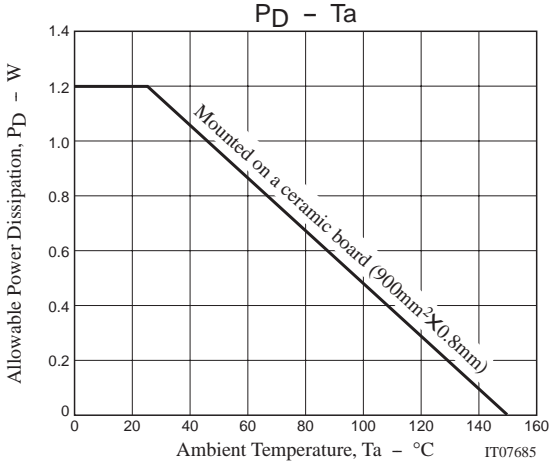
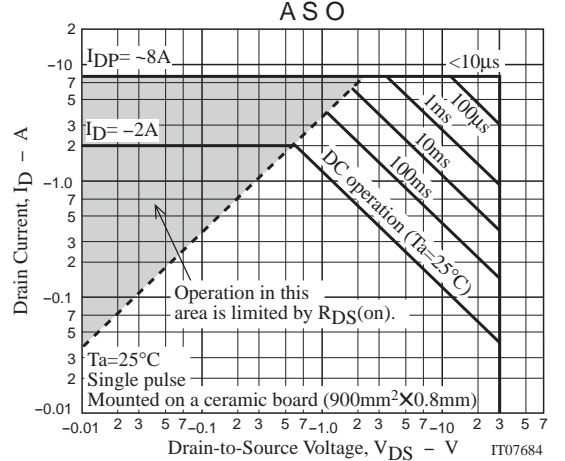
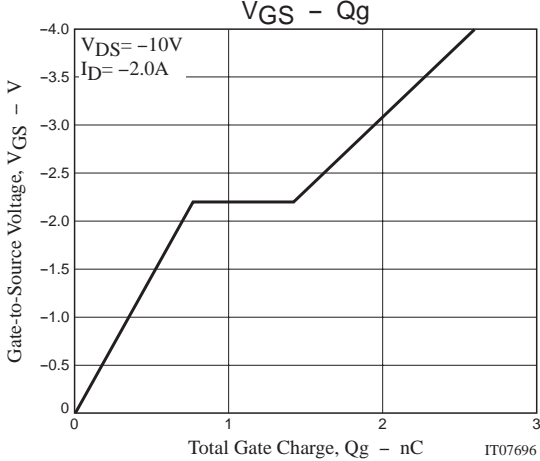
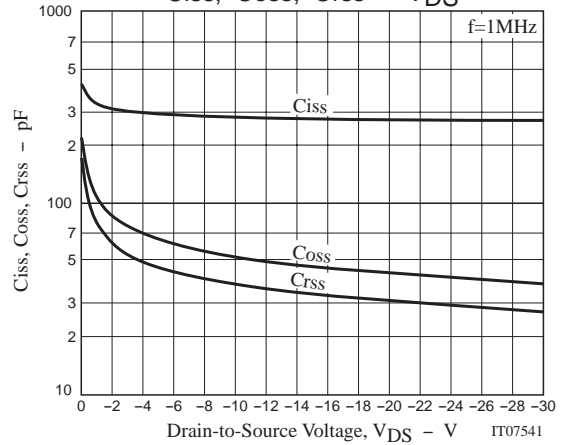
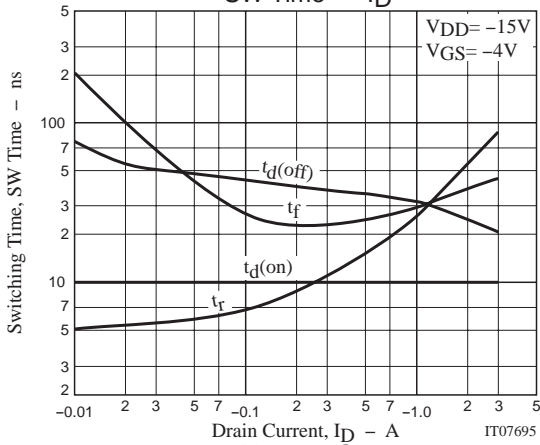
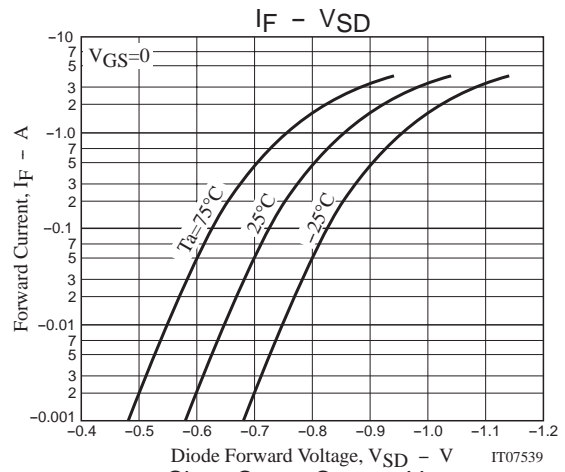
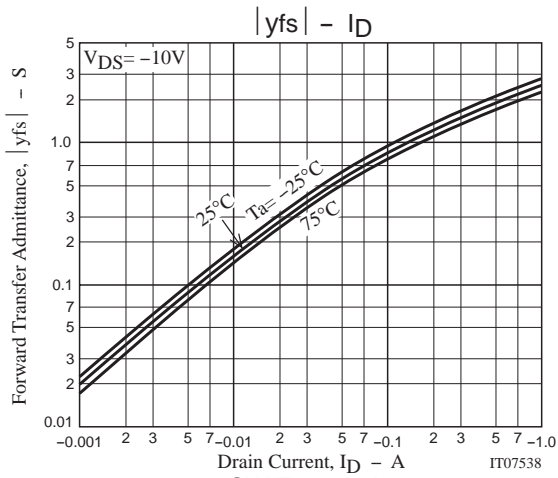
unit : mm

2151A



Switching Time Test Circuit





Note on usage : Since the CPH6329 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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